

Abstract of the Disclosure

The nonvolatile ferroelectric memory device comprises a plurality of cell array blocks; a plurality of drivers; 5 and a plurality of decoders connected to the cell array blocks, respectively, wherein the decoder comprises a first sub-decoder for generating the decoding signal applied to the driver and a second sub-decoder for generating a signal selecting the driver. As a result, the nonvolatile 10 ferroelectric memory device can reduce the area of the device and improve the driving speed.